



LAL



KEK



Tsukuba HEP



Workshop on France-Japan and France-Korea Particle Physics Laboratories

Continuation of the D RD 15 project:

Innovative design concepts in P-bulk Planar Pixel Sensor R&D project

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Introduction

- **Collaboration**

- Planar type Silicon Pixel detector R&D for ATLAS detector upgrade in France-Japan collaboration

- **Goals**

- Performance : evaluate & improve sensor design for radiation tolerance up to $3 \times 10^{15} n_{eq}/cm^2$ fluence.
- Productions : work on common sensor productions

Active Edge

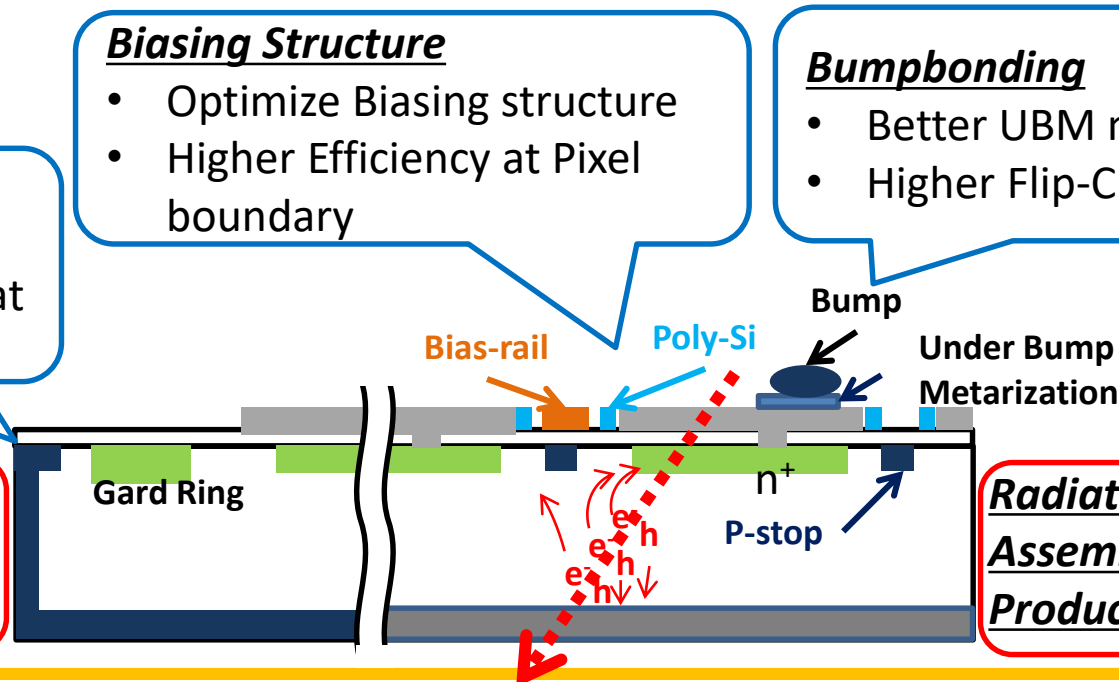
- Smaller Edge size
- Higher Efficiency at Edge region

Biasing Structure

- Optimize Biasing structure
- Higher Efficiency at Pixel boundary

Bumpbonding

- Better UBM material
- Higher Flip-Chip Yield



Simulation

- Doping concentration
- Charge collection

Radiation Tolerance
Assembly
Production...

Framework : ATLAS Upgrade for HL-LHC

- **High Luminosity LHC (HL-LHC)**

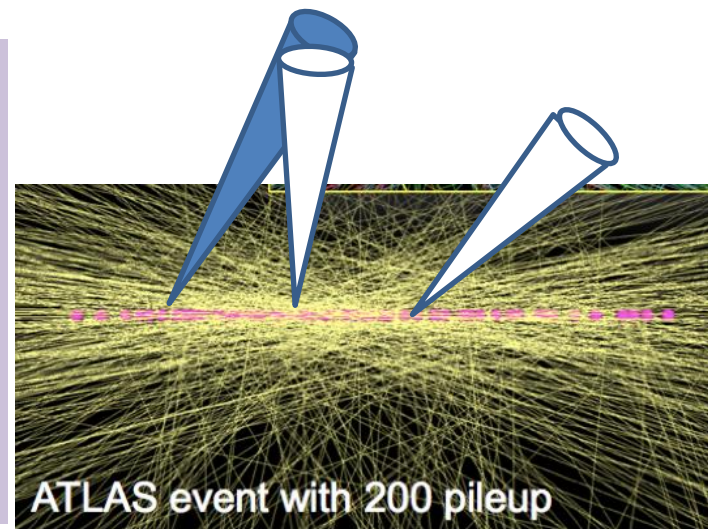
- Start around 2026- with new crab cavity in the interaction region.
- Target : $\sqrt{s}=14\text{TeV}$ $L=5\times 10^{34}\text{cm}^{-2}\text{s}^{-1}$ $\int Ldt=3000-4000\text{fb}^{-1}$
- Physics program focus on the precise measurements of the Higgs couplings (e.g. Y_{τ} , Y_b and λ_{HHH}) and BSM searches.

- **Tracking detector is key element**

- To keep B/ τ -tagging performance up to $\mu=200$ pileup in an event.
- Need to launch **innovative solution for detectors**, mechanics, efficient triggering and advanced analysis technics.

The ATLAS upgrade plans full replacement of Inner Tracker

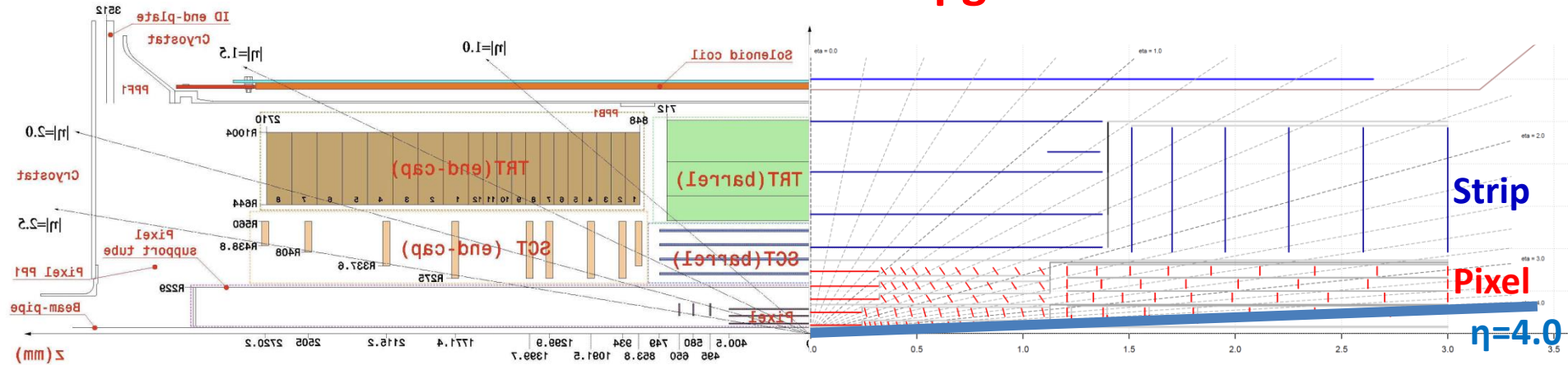
- All silicon tracker (Pixel & Microstrip)
- **Requirements for Pixel detector**
 - Pixel Size : 50 μm x 50 μm (or 25 μm x 100 μm)
 - Radiation @ outer layer : $3\times 10^{15}n_{\text{eq}}/\text{cm}^2$
 - Thickness : 100 or 150 μm
 - Low noise (<100e) \rightarrow 600e stable threshold
 - High Readout Rate : 5.2Gbps (or 4x1.28Gbps)



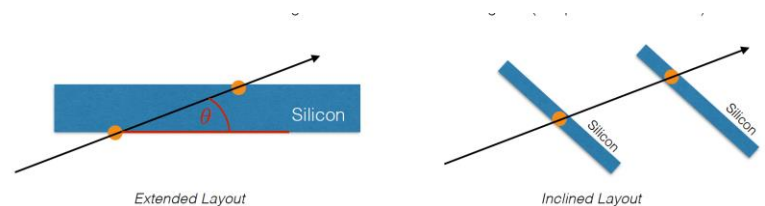
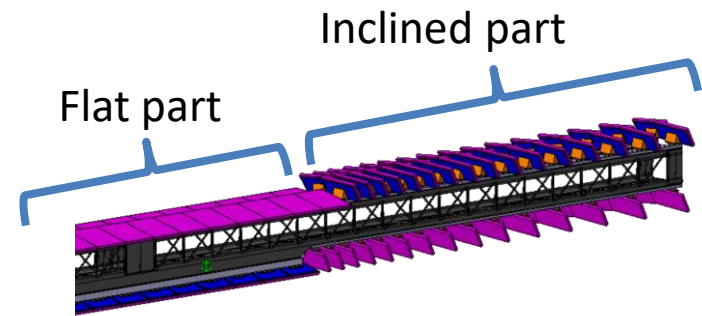
ATLAS inner tracker(ITK) project for HL-LHC

Current ATLAS Detector

ITK upgrade detector



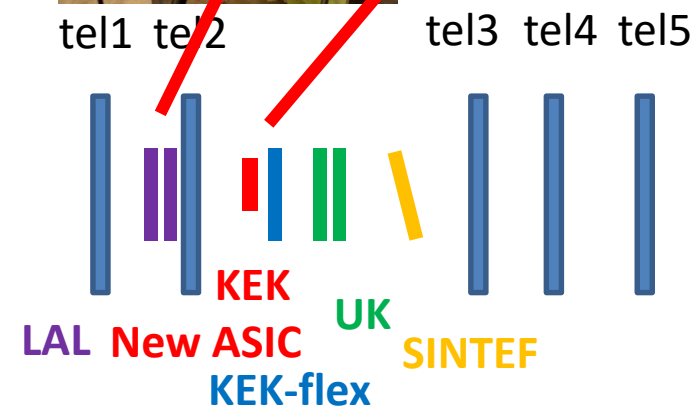
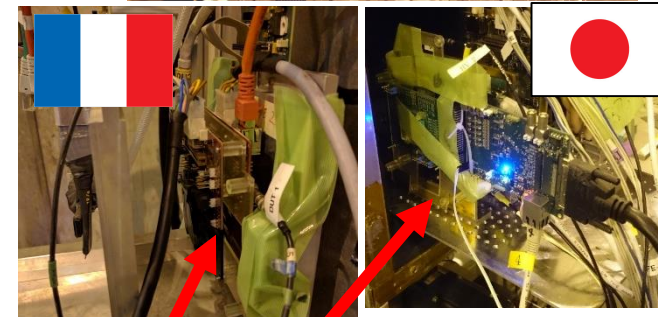
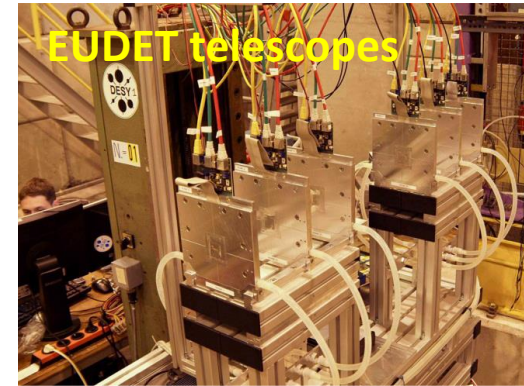
- Larger coverage area
 - Pixel : current 2.7m^2 → **upgrade 8.2m^2**
 - Strip : current 62m^2 → **upgrade 193m^2**
- Higher Forward coverage
 - Current $\eta < 2.5$ → **upgrade $\eta < 4.0$**
 - **Better Pileup removal**
- Mechanics : inclined
 - Reduce material
 - Higher tracking resolution.



Facility and expertise

Testbeam campaign

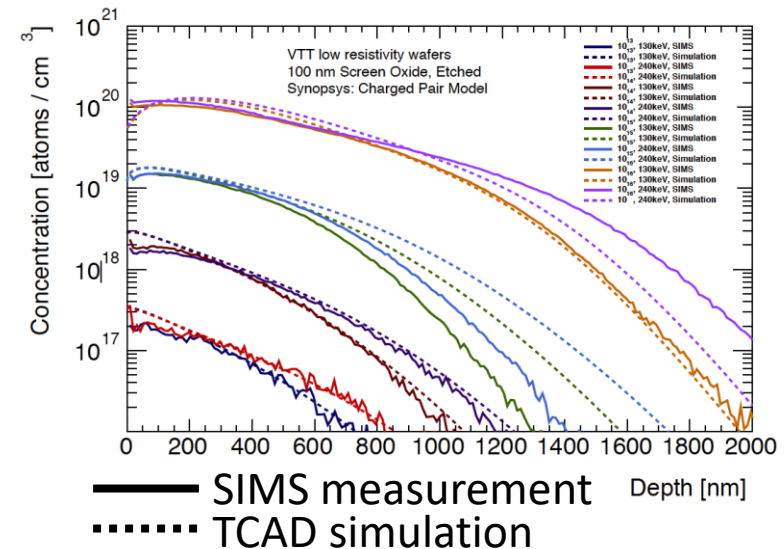
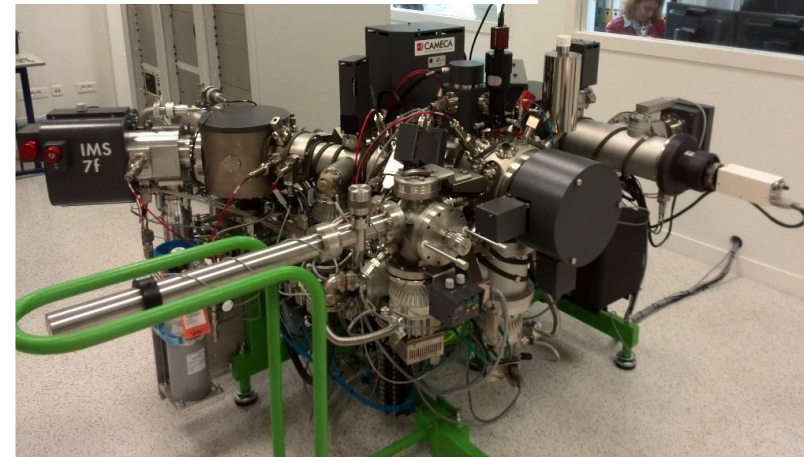
- **Extremely important to test device performance**
 - DAQ and operation
 - In-pixel and/or Edge efficiency
- Testbeam facility
 - **CERN SPS : 120GeV π^+ beam**
 - DESY : 4-5GeV e^+ beam
 - SLAC : 5-13GeV e^- beam
 - FNAL : 120GeV proton beam
- Telescope planes (Track pointing to device)
 - EUDET based on MIMOSA26 monolithic CMOS detector placed in beamline at CERN/DESY/SLAC (**$\sim 3\mu\text{m}$ pointing resolution**).
 - Huge experience of the testbeam operation as having testbeam 3-4 times a year
- **Example** : November testbeam @CERN
 - LAL&KEK devices are in the same runs together with UK, Norway's samples.
 - Excellent data taking was achieved.



Secondary Ion Mass Spectrometry and Simulation

- SIMS measurement
 - Analytical technique to characterize the impurities near surface (<30um) by ionized secondary particles.
 - Good detection sensitivity for **B, P, Al, As, Ni, O, Si** etc down to 10^{13} atoms/cm³ with 1-5nm depth resolution.
- Synopsys TCAD simulation
 - Process simulation:
 - Simulate implantation and resulting concentrations.
 - **Can compare to SIMS result.**
 - Device Simulation :
 - Simulate Electric field to understand the performance of silicon device.
 - Possible to perform simulation for charge correction of MIP signal.

SIMS system at Versailles





CYRIC : Irradiation Facility in Japan

CYRIC@Tohoku Univ.

- An irradiation facility with **70MeV proton beam** (**~1μA beam current**).
 - 3-5 hours for $3 \times 10^{15} n_{eq}/cm^2$ irradiation with (600nA beam)
- This allows 2-3 pixel modules with Al plate at the same time(3% E loss/module).
- Operated at **-15°C temprature** with dry N₂ gas.
- Scanning over full pixel range during irradiation.

LAL's Active Edge Pixel Modules

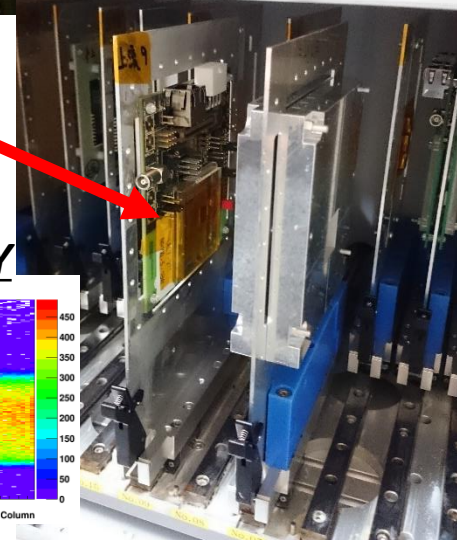
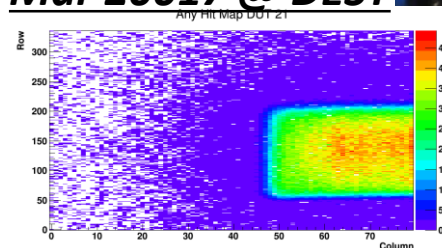
- Irradiated LAL's module twice in 2016 and 2017.
- First irradiation, observed disconnection of bumps after irradiation.
- **Second irradiation, it was successfully done and measured the device at DESY testbeam in March 2017.**



Feb 2017

LAL's Pixel Mod.
(Active Edge)

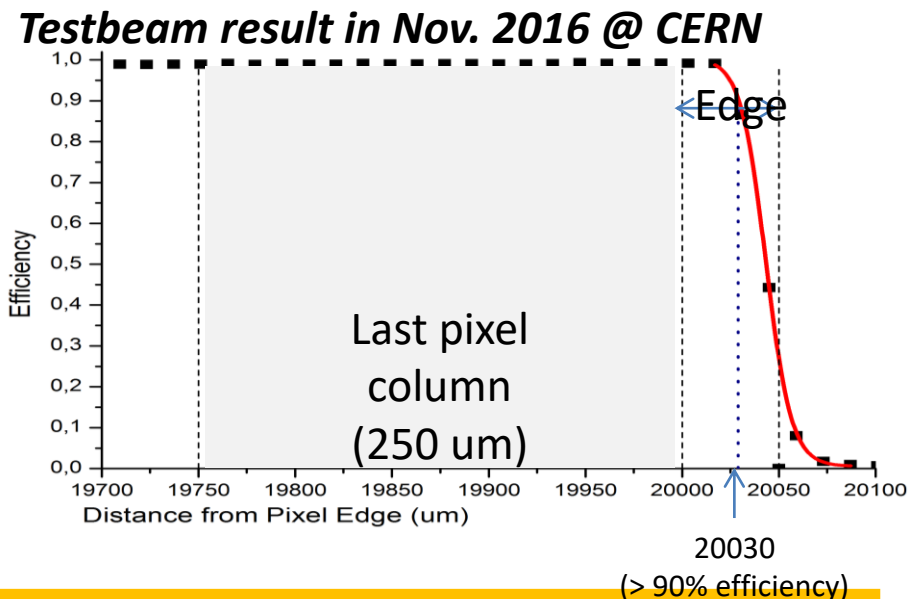
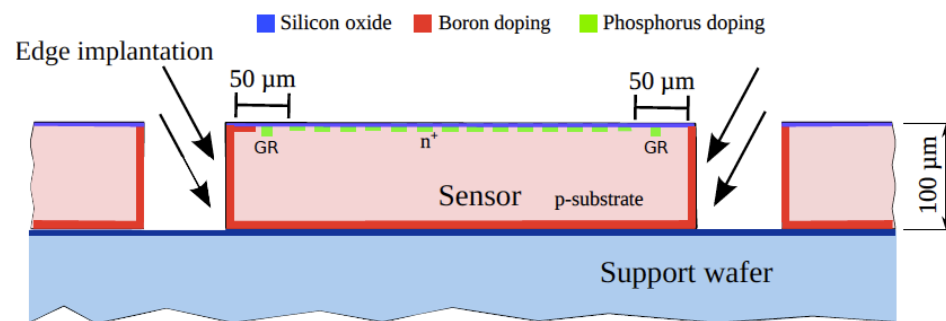
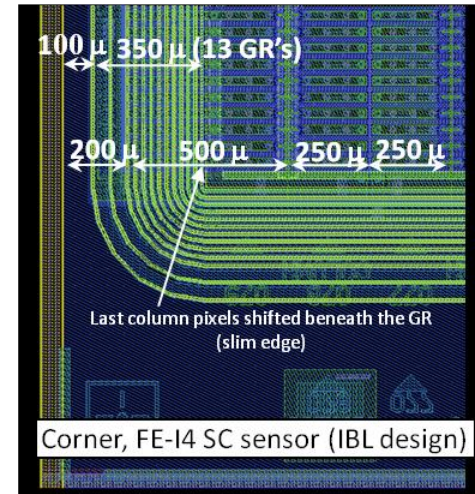
Mar 20017 @ DESY



Sensor technology improvement

Active Edge

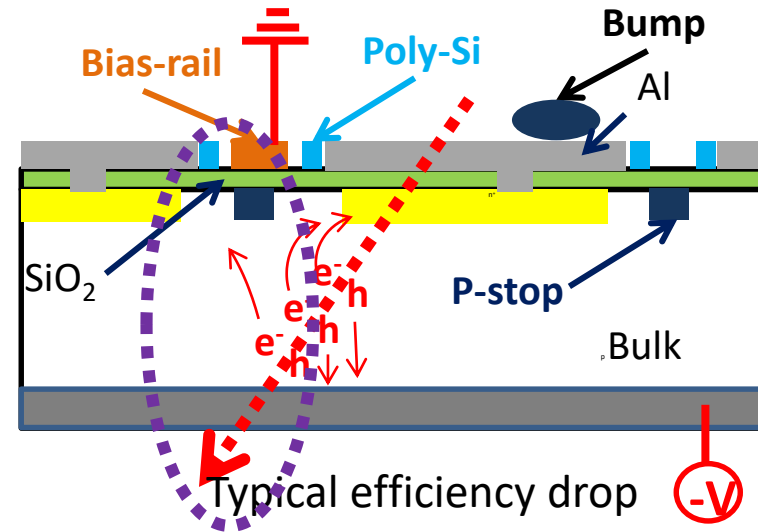
- Active edge designs for planar pixels.
 - To decrease the Edge inefficiency, active edge process has been developed over 4 years with VTT.
 - To achieve a fully efficient and slim edge sensor, edge implantation (Boron) is performed.
 - 100-200um thick sensor with this active edges makes it a very attractive candidates for the inner layer(s).
 - Guard ring types are optimized.



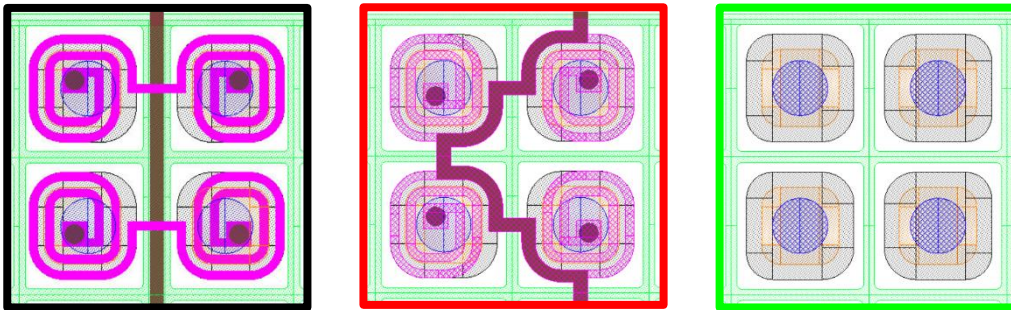
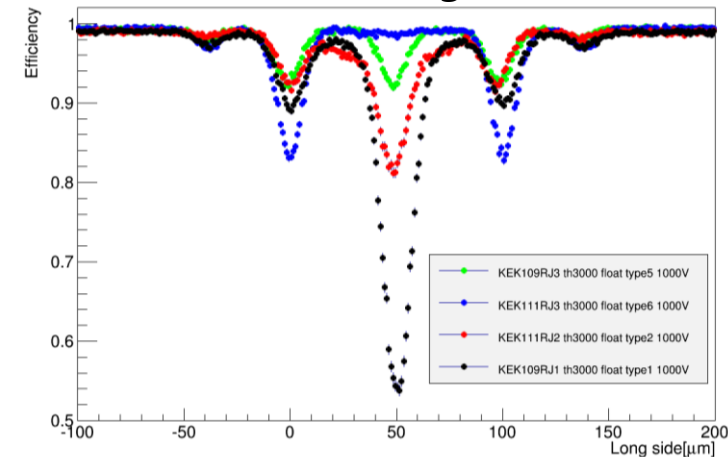


Biassing structure optimization

- Biassing Structure
 - To apply bias voltage before bumpbonding biasing structure (bias rail and resistor/punch through) to each pixel is necessary to make it GND.
 - **On the other hand we observed Efficiency drop under the structure due to field effect.**
- Charge sharing
 - On the corner of pixel MIP charge split to 4 pixels resulting lower efficiency.
- Biassing structure optimization and lower noise readout chip (TSMC 65nm) are tested.
 - **Better Efficiency with optimized bias rail path.**
 - Trying to figure out low threshold data with new chips.



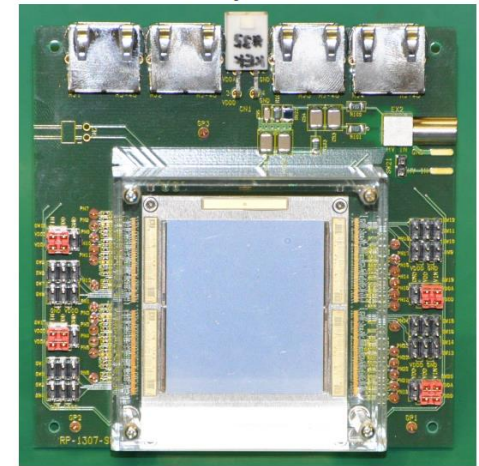
Testbeam result in Aug. 2016 @ CERN



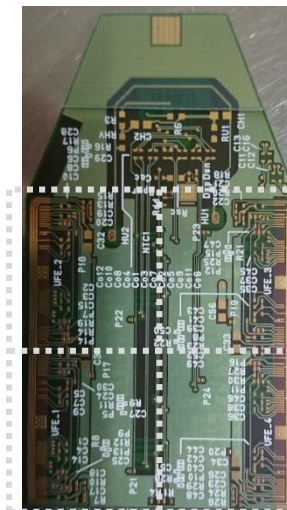


Module Assembly

4 Chip Card



- Bump Bonding Technology has been developed.
 - Optimized under bump metallization (UBM)
 - Optimization of parameters for flip-chip.
 - **Yield of bump bonding is almost 100% for last 2 years(>60 ASICs).**
 - **Stability against thermal cycling (-40,40°C) performed w/o bump disconnection.**
- Towards Integration, Flex readout circuits have been developed.
 - **Quad(4 ASICs) and double(2 ASICs) module flex have been designed and produced in Japan.**
 - Alignment tools for gluing and wire bonding are in development.



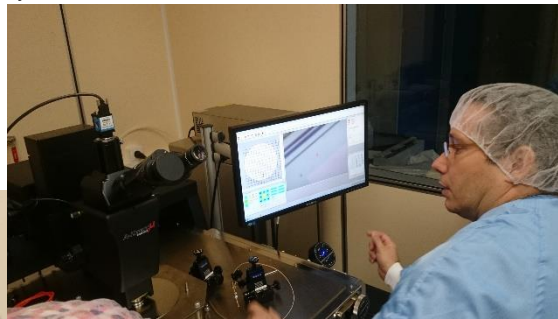
Exchange Experience

Visit LAL in 2016

Kazuyuki Sato, Junki Suzuki, Hitomi Tokutake, Hiromi Sawai and K.N.

Original aim is to perform SIMS measurement @ Versailles but it was temporary broken unfortunately.

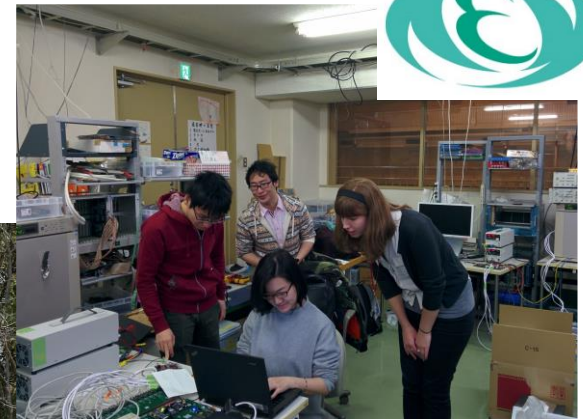
Visiting probe-station, SMD lab etc.



Visit KEK in 2015

Clara Nelist

After irradiation of LAL's module in Japan, testing for the device as well as visiting J-park @ Tokai

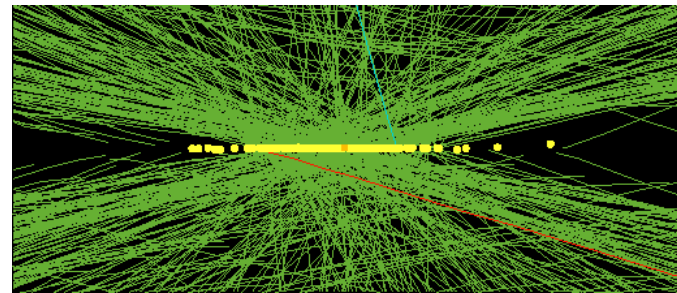


Good opportunity to share expertise and effort.

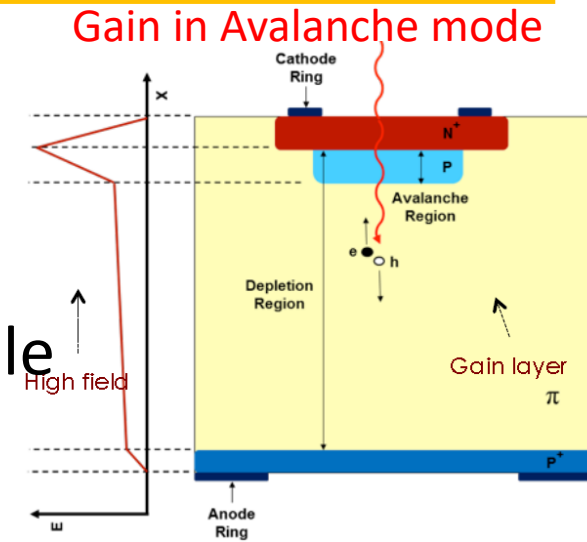
Another layer of Collaboration? : LGAD

Low Gain Avalanche Detectors

- To solve pileup issue in future high luminosity hadron collider, good time resolution detector is important.
- The **~50ps** time resolution makes it possible to identify each collision in an event.



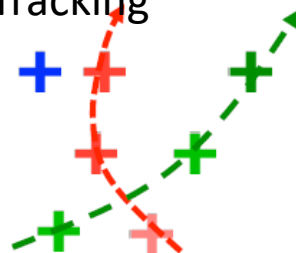
- Time resolution
 - Smaller time walk (higher field)
 - Smaller time jitter (low noise)
- p+ layer beneath n+ implant creates ~300kV/cm electric field (Gain ~ 10)



Detector Hit



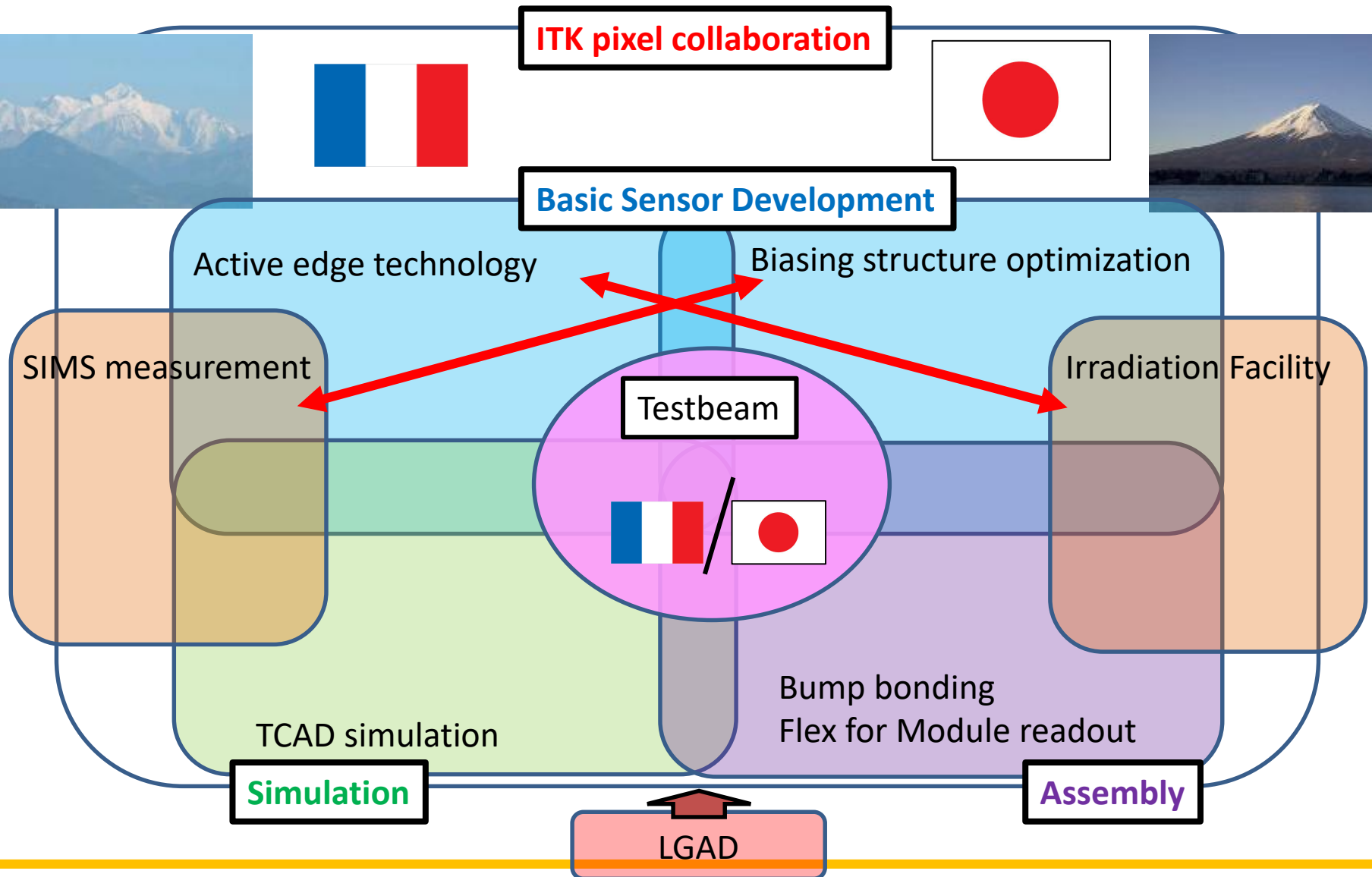
Tracking



CNM/FBK/HPK produced devices

- LAL group : Simulation&Testing CNM device
- Tsukuba group : Testing HPK device

Sharing of the work



Conclusion

- **French and Japanese Groups are committed in an ambitious R&D program inside the ATLAS ITK effort for HL-LHC, where we will face challenging issues:**
Major issue is to Built an innovative granular thin pixel planar detector.
 - Find the best sensor layout ingredients for high charge collection efficiency.
 - Explore productions with active edge and optimized biasing structure which will exhibit the best performance.
 - Develop robust radiation hard solutions to cope with HL-LHC irradiation fluences.
- **Thus our aim is to enhance and reinforce LAL-FR/Japan collaboration to built the future P bulk Planar Pixel Sensors for ATLAS tracker for HL-LHC. We intend to increase the :**
 - Synergy in terms of P bulk sensor design, characterization and testing (Clean room, Test-Beam, irradiation facility)
 - Understand the behavior of heavily irradiated Planar Pixel Sensors
 - Share expertise and efforts (TCAD simulation, SIMS, Irradiation etc...).
- **Now in application of Japanese funding program for "Advancing Strategic International Networks to Accelerate the Circulation of Talented Researchers."**
LAL is also partner other such Japanese research program.

Budget request 2017

Funding Request from France					Funding Request from Japan				
Description	€/unit	Nb of units	Total (€)	Requested to	Description	k¥/unit	Nb of units	Total (k¥)	Requested to
Visit to KEK/Tsukuba (2 seniors)	150 / day	5 day	1500	FJPPL	Student Stay at LAL	100 / week	4 weeks	400	FJPPL/LAL
Student Stay in KEK/Tsukuba	1000/month	2 weeks	500	KEK/Tsukuba	Travel+per-diem (Japan-CERN)	400	1	400	FJPPL
Travels	900	2	1800	FJPPL	Travel+per-diem (CERN-LAL)	50	4	200	FJPPL
Total			5850		Total			1000	

Additional Funding from France			Additional Funding from Japan		
Provided by / requested to	Type	€	Provided by / requested to	Type	k¥
LAL / ATLAS PIXEL	TCAD SIM license	400	Tsukuba / ATLAS PIXEL	Travel to CERN	2100
LAL / ATLAS PIXEL	Silicon wafer production	4000	Tsukuba / ATLAS PIXEL	Various expenditure	600
LAL / ATLAS PIXEL	Readout card	1500			
Total		5900	Total		2700

backup

Members

FJPPL (TYL) application 2016-2017

Fiscal year April 1st 2016– March 31st 2017

Please replace the red examples by the appropriate data in black

ID¹:	Title: Innovative design concepts in P Bulk Planar Pixel Sensors					
Leader Members	French Group			Japanese Group		
	Name	Title	Lab./Organis.²	Name	Title	Lab/Organis.³
	Leader : A. Lounis	Dr.	LAL/IN2P3	Leader : K. Hara	Dr.	U. Tsukuba
	P. Petroff	Dr.	LAL/IN2P3	K. Nakamura	Dr.	KEK
	R. Tanaka	Dr.	LAL/IN2P3	Y. Unno	Dr.	KEK
	D. Varouchas	Dr	LAL/IN2P3	Y. Ikegami	Dr.	U. Tsukuba/KEK
	D. Hohov	PhD	LAL/IN2P3	H. Okawa	Dr.	U. Tsukuba

Budget request in 2017

Funding Request from France				
Description	€/unit	Nb of units	Total (€)	Requested to ⁴ :
Visit to KeK/Tsukuba (2 seniors)	150/day	5 days	1500	FJPPL
Student Stay in KeK/Tsukuba	1000/month	2 weeks	500	KEK /TSUKUBA
Travels	900	2	1800	FJPPL
Total			5850	
Funding Request from KEK				
Description	¥/Unit	Nb of units	Total (¥)	Requested to:
Student Stay at LAL	100/week	4 weeks	400	FJPPL/LAL
Travel+ per-diem (Japan-CERN)	400	1	400	FJPPL
Travel+ per-diem (CERN-LAL)	50	4	200	FJPPL
Total			1000	

Additional Funding from France			Additional Funding from Japan		
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